

# Joonas Hilska

## List of Publications by Year in descending order

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Version: 2024-02-01

16  
papers

115  
citations

1307594

7  
h-index

1372567

10  
g-index

16  
all docs

16  
docs citations

16  
times ranked

111  
citing authors

#	ARTICLE	IF	CITATIONS
1	Optical properties of n- and p-type modulation doped GaAsBi/AlGaAs quantum well structures. Journal of Alloys and Compounds, 2018, 739, 987-996.	5.5	16
2	Analysis of GaAsBi growth regimes in high resolution with respect to As/Ga ratio using stationary MBE growth. Journal of Crystal Growth, 2019, 511, 33-41.	1.5	13
3	Highly uniform GaSb quantum dots with indirect→direct bandgap crossover at telecom range. APL Materials, 2021, 9, .	5.1	12
4	Nanohole Etching in AlGaSb with Gallium Droplets. Crystal Growth and Design, 2021, 21, 1917-1923.	3.0	11
5	Electronic transport in n-type modulation-doped AlGaAs/GaAsBi quantum well structures: influence of Bi and thermal annealing on electron effective mass and electron mobility. Semiconductor Science and Technology, 2020, 35, 025009.	2.0	10
6	Optical properties of GaAs <sub>1-x</sub> Bi <sub>x</sub> /GaAs quantum well structures grown by molecular beam epitaxy on (100) and (311)B GaAs substrates. Semiconductor Science and Technology, 2018, 33, 124015.	2.0	7
7	Impact of Bi incorporation on the evolution of microstructure during growth of low-temperature GaAs:Bi/Ga(As,Bi) layers. Journal of Applied Physics, 2019, 126, 085305.	2.5	7
8	Raman spectroscopy of GaSb <sub>1-x</sub> Bi <sub>x</sub> alloys with high Bi content. Applied Physics Letters, 2020, 116, .	3.3	6
9	Exciton localization and structural disorder of GaAs <sub>1-x</sub> Bi <sub>x</sub> /GaAs quantum wells grown by molecular beam epitaxy on (311)B GaAs substrates. Semiconductor Science and Technology, 2018, 33, 084002.	2.0	5
10	Epitaxial phases of high Bi content GaSbBi alloys. Journal of Crystal Growth, 2019, 516, 67-71.	1.5	5
11	Power loss mechanisms in n-type modulation-doped AlGaAs/GaAsBi quantum well heterostructures. Semiconductor Science and Technology, 2020, 35, 095038.	2.0	5
12	The Role of Epitaxial Strain on the Spontaneous Formation of Bi-Rich Nanostructures in Ga(As,Bi) Epilayers and Quantum Wells. Nanoscience and Nanotechnology Letters, 2017, 9, 1132-1138.	0.4	5
13	A quantitative analysis of electronic transport in n- and p-type modulation-doped GaAsBi/AlGaAs quantum well structures. Semiconductor Science and Technology, 2021, 36, 115017.	2.0	4
14	The role of As species in self-catalyzed growth of GaAs and GaAsSb nanowires. Nanotechnology, 2020, 31, 465601.	2.6	4
15	Optimization of Ohmic Contacts to p-GaAs Nanowires. Nanoscale Research Letters, 2019, 14, 344.	5.7	3
16	High-Field Electron Drift Velocity in n-Type Modulation-Doped GaAs <sub>0.96</sub> Bi <sub>0.04</sub> Quantum Well Structure. Physica Status Solidi - Rapid Research Letters, 2022, 16, .	2.4	2